



P-Channel Enhancement-Mode Vertical DMOS FET

Features

- ▶ High input impedance and high gain
- ▶ Low power drive requirement
- ▶ Ease of paralleling
- ▶ Low C_{iss} and fast switching speeds
- ▶ Excellent thermal stability
- ▶ Integral source-drain diode
- ▶ Free from secondary breakdown

Applications

- ▶ Logic level interfaces - ideal for TTL and CMOS
- ▶ Solid state relays
- ▶ Analog switches
- ▶ Power management
- ▶ Telecom switches

Ordering Information

Part Number	Package Option	Packing
TP5335K1-G	TO-236AB (SOT-23)	3000/Reel

-G denotes a lead (Pb)-free / RoHS compliant package.
 Contact factory for Wafer / Die availability.
 Devices in Wafer / Die form are lead (Pb)-free / RoHS compliant.

Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	$\pm 20V$
Operating and storage temperature	$-55^{\circ}C$ to $+150^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Typical Thermal Resistance

Package	θ_{ja}
TO-236AB (SOT-23)	$203^{\circ}C/W$

General Description

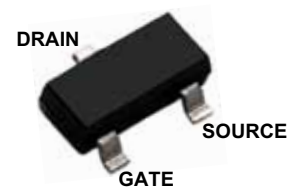
The Supertex TP5335 is a low threshold enhancement-mode (normally-off) transistor utilizing an advanced vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Product Summary

BV_{DSS}/BV_{DGS}	$R_{DS(ON)}$ (max)	$V_{GS(th)}$ (max)
-350V	30Ω	-2.4V

Pin Configuration



TO-236AB (SOT-23)

Product Marking

P3SW W = Code for week sealed
 — = "Green" Packaging

Package may or may not include the following marks: Si or

TO-236AB (SOT-23)

Thermal Characteristics

Package	I_D (continuous) [†]	I_D (pulsed)	Power Dissipation @ $T_A = 25^\circ\text{C}$	I_{DR} [†]	I_{DRM}
TO-236AB (SOT-23)	-85mA	-400mA	0.36W	-85mA	-400mA

Notes:

[†] I_D (continuous) is limited by max rated T_J .

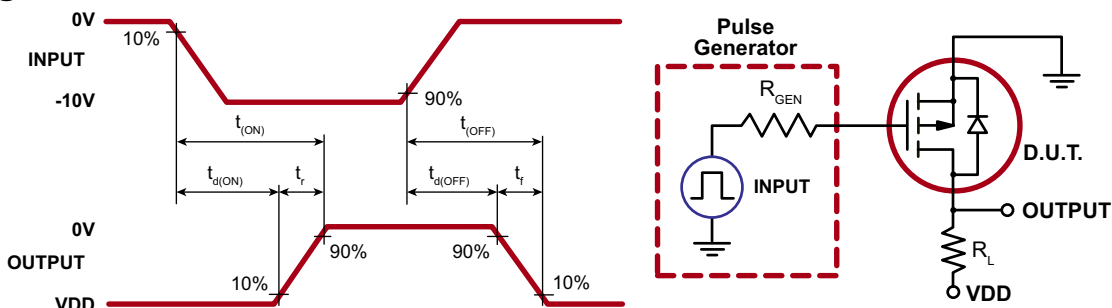
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	-350	-	-	V	$V_{GS} = 0V, I_D = -100\mu\text{A}$
$V_{GS(TH)}$	Gate threshold voltage	-1.0	-	-2.4	V	$V_{DS} = V_{GS}, I_D = -1.0\text{mA}$
$\Delta V_{GS(TH)}$	Change in $V_{GS(TH)}$ with temperature	-	-	4.5	mV/°C	$V_{DS} = V_{GS}, I_D = -1.0\text{mA}$
I_{GSS}	Gate body leakage current	-	-	-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I_{DSS}	Zero gate voltage drain current	-	-	-10	μA	$V_{DS} = \text{Max rating}, V_{GS} = 0V$
		-	-	-1.0	mA	$V_{DS} = 0.8 \text{ Max Rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$
		-	-	-5.0	nA	$V_{GS} = 0V, V_{DS} = -330V$
$I_{D(ON)}$	On-state drain current	-200	-	-	mA	$V_{GS} = -4.5V, V_{DS} = -25V$
		-400	-	-		$V_{GS} = -10V, V_{DS} = -25V$
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	-	75	Ω	$V_{GS} = -4.5V, I_D = -150\text{mA}$
		-	-	30		$V_{GS} = -10V, I_D = -200\text{mA}$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	1.7	%/°C	$V_{GS} = -10V, I_D = -200\text{mA}$
G_{FS}	Forward transconductance	125	-	-	mmho	$V_{DS} = -25V, I_D = -200\text{mA}$
C_{ISS}	Input capacitance	-	-	110	pF	$V_{GS} = 0V, V_{DS} = -25V, f = 1\text{MHz}$
C_{OSS}	Common source output capacitance	-	-	60		
C_{RSS}	Reverse transfer capacitance	-	-	22		
$t_{d(ON)}$	Turn-on delay time	-	-	20	ns	$V_{DD} = -25V, I_D = -150\text{mA}, R_{GEN} = 25\Omega,$
t_r	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	25		
t_f	Fall time	-	-	25		
V_{SD}	Diode forward voltage drop	-	-	-1.8	V	$V_{GS} = 0V, I_{SD} = -200\text{mA}$
t_{tr}	Reverse recovery time	-	800	-	ns	$V_{GS} = 0V, I_{SD} = -200\text{mA}$

Notes:

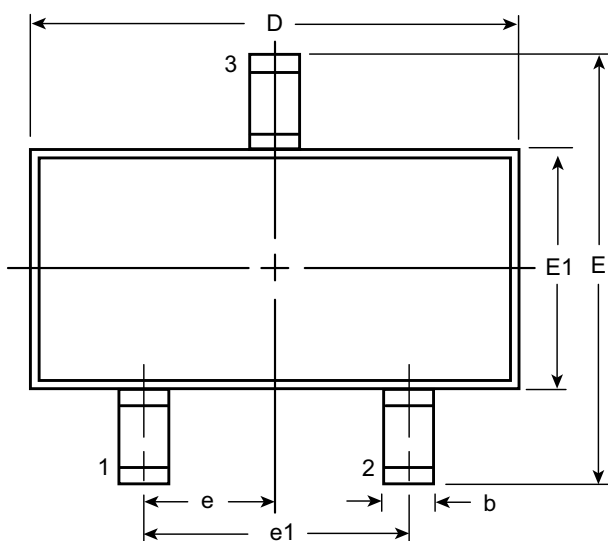
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: $300\mu\text{s}$ pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

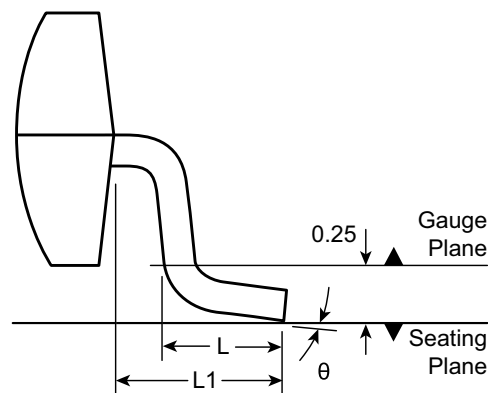


3-Lead TO-236AB (SOT-23) Package Outline (K1)

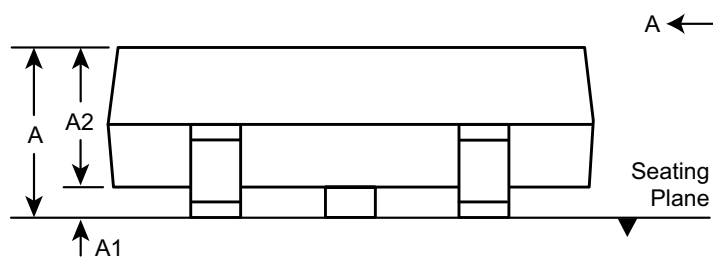
2.90x1.30mm body, 1.12mm height (max), 1.90mm pitch



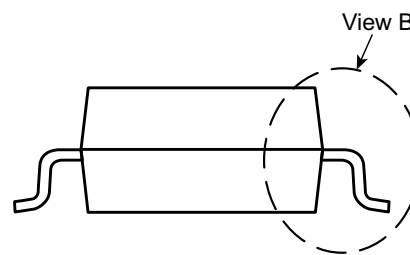
Top View



View B



Side View



View A - A

Symbol	A	A1	A2	b	D	E	E1	e	e1	L	L1	θ	
Dimension (mm)	MIN	0.89	0.01	0.88	0.30	2.80	2.10	1.20	0.95 BSC	1.90 BSC	0.20 [†]	0.54 REF	0°
	NOM	-	-	0.95	-	2.90	-	1.30					-
	MAX	1.12	0.10	1.02	0.50	3.04	2.64	1.40					0.60

JEDEC Registration TO-236, Variation AB, Issue H, Jan. 1999.

[†] This dimension differs from the JEDEC drawing.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO236ABK1, Version C041309.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <http://www.supertex.com/packaging.html>.)

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